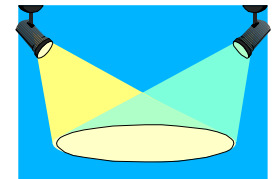




CAD Tool Requirements for Next Generation On-Chip Signal Integrity Issues

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Agenda

- Circuit failure criteria
 - functional
 - timing
- Noise sources and evaluation techniques
 - coupling
 - common mode
 - differential power supply
 - charge sharing
 - leakage
- Noise summation process
- Future tool needs

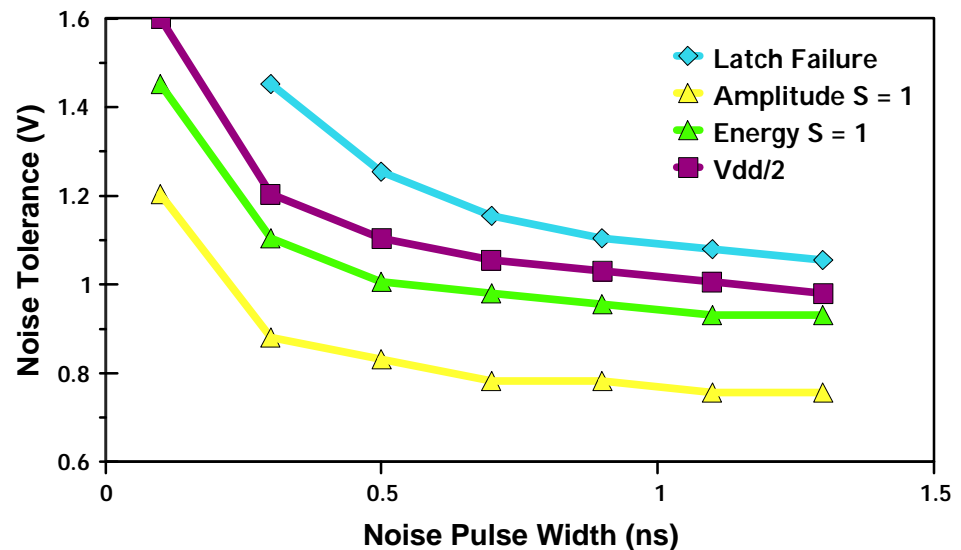
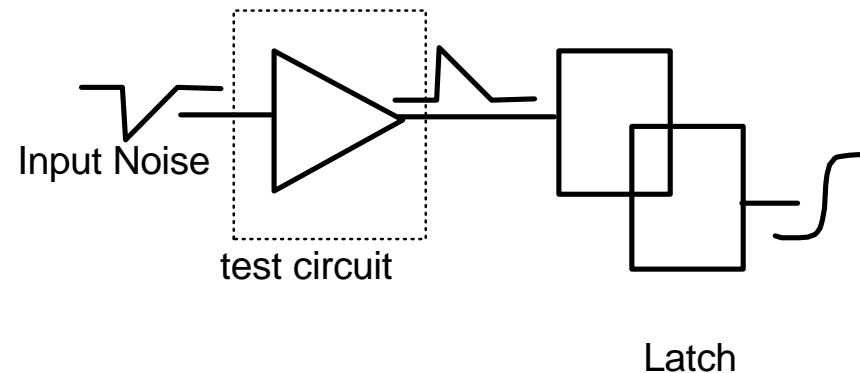
Circuit Noise Failure Criteria(functional)

■ Data corruption at storage node

- non-recovering circuits
 - dynamic nodes
 - latches
- exceed circuit noise margin

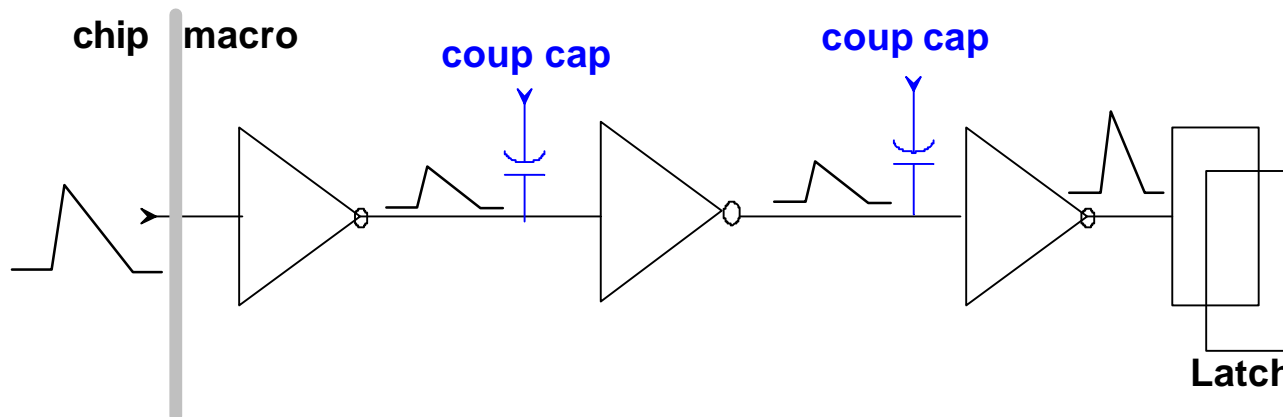
■ Noise margin definitions

- AC noise margins
 - set/reset latch
 - sensitivity criteria
 - $\Delta\Phi_{out}(t)/\Delta\Phi_{in}(t)$
 - ◆ amplitude
 - ◆ energy
 - ◆ etc.



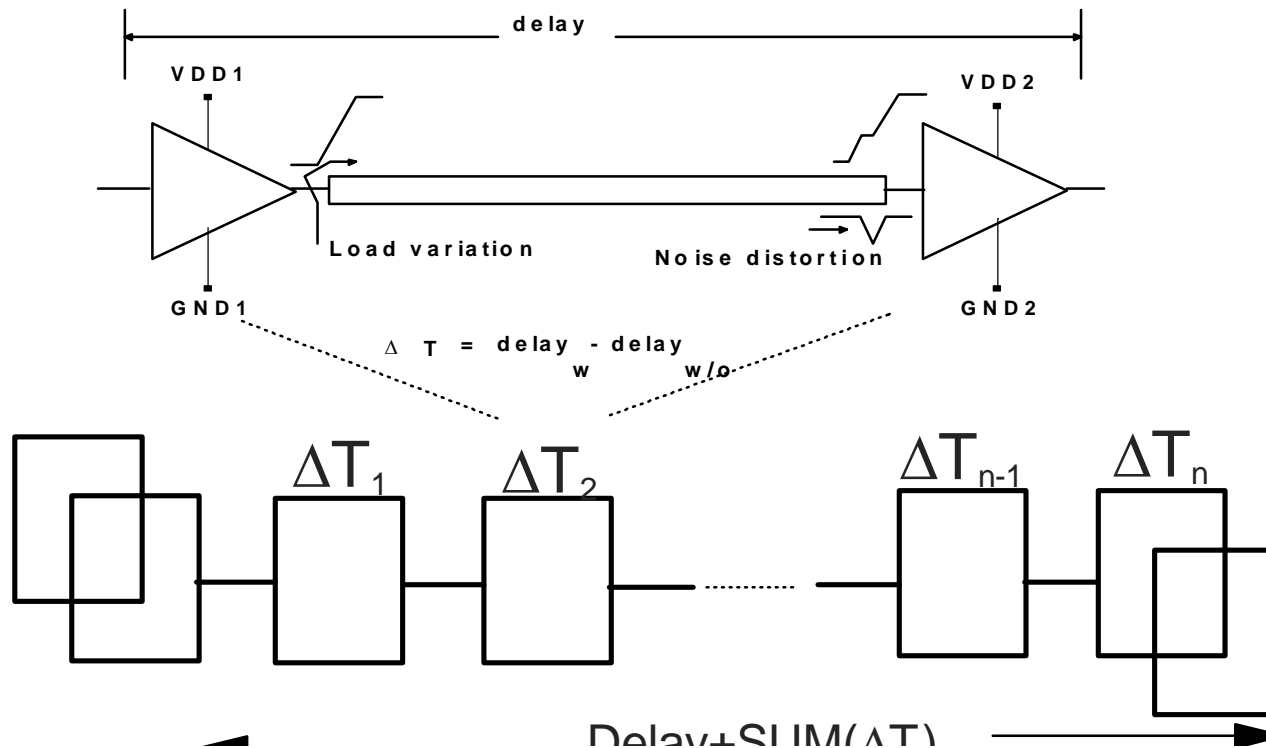
Circuit Noise Failure Criteria(functional)

- Path evaluation
 - ▶ stage to stage noise propagation
 - circuit based noise margins conservative
 - "static" noise verification technique
 - noise injection @ circuit input
 - ◆ summation of noise sources
 - noise propagation @ circuit output
 - ▶ transistor based simulations
 - ▶ tools: IBMmlsa(IBM internal), CADMOS



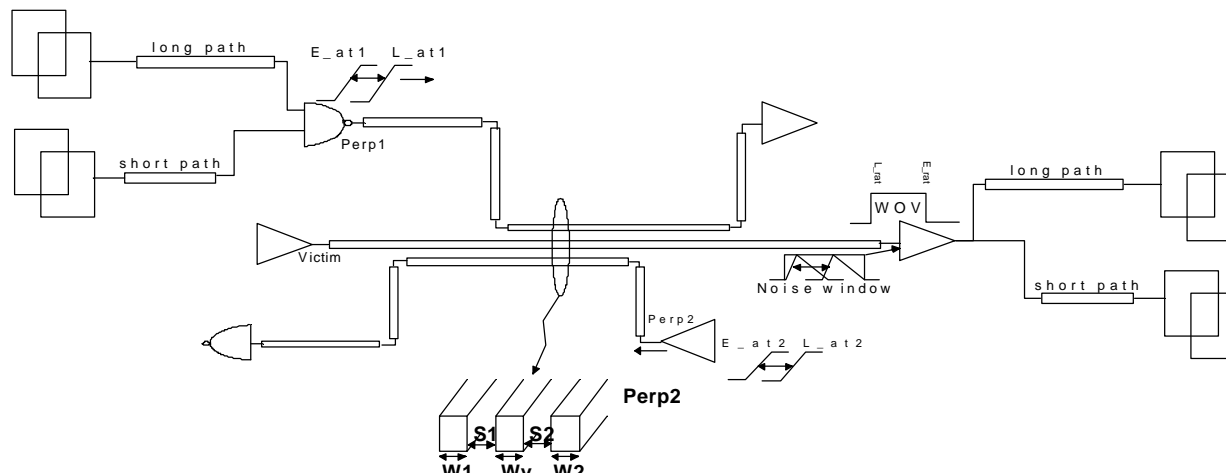
Circuit Noise Failure Criteria(Performance)

- Net based noise jitter effects
 - delay variations(ΔT) due to net coupling and/or power supply noise
 - rise time distortion at receiving circuit
 - load variation at driving circuit
 - wire delay variations
- Noise Jitter accumulates through logic stages in a path



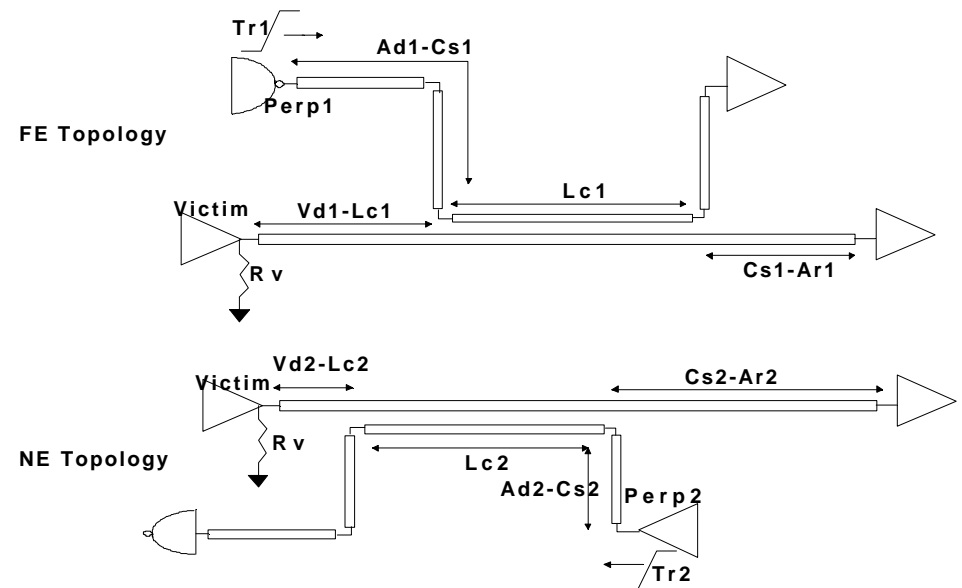
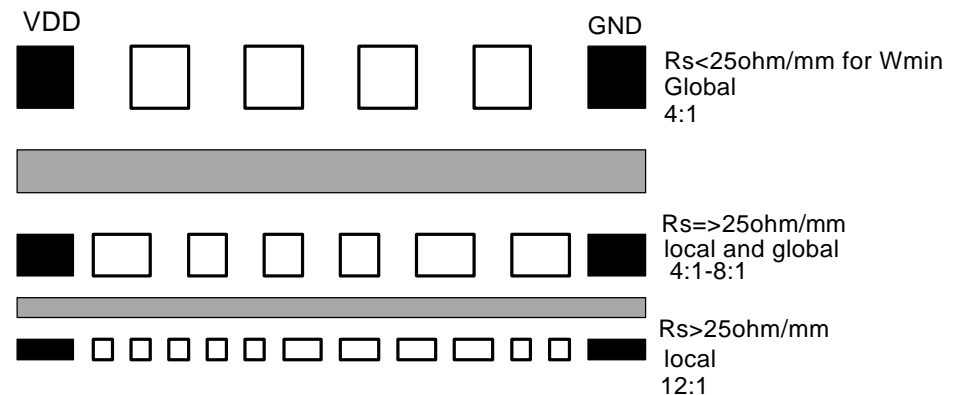
Coupling Noise

- RC coupling
 - high wire resistance
 - 90% of net population
- RLC coupling
 - RC model error > 20%
 - $R \cdot L / 2 \cdot Z_0 < \sim 1.5$
 - $Z_{drv} \cdot C_t < 3 \cdot R \cdot C \cdot L^2 / 2$
 - frequency dependent RLC
 - proximity effects
 - time and noise critical nets
- Multiple coupling interactions
 - horizontal and vertical
- Timing dependency
 - noise source alignment
 - quiet net susceptibility window(WOV)



Coupling Noise Evaluation Dependencies

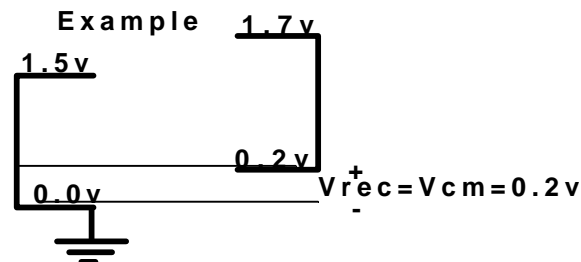
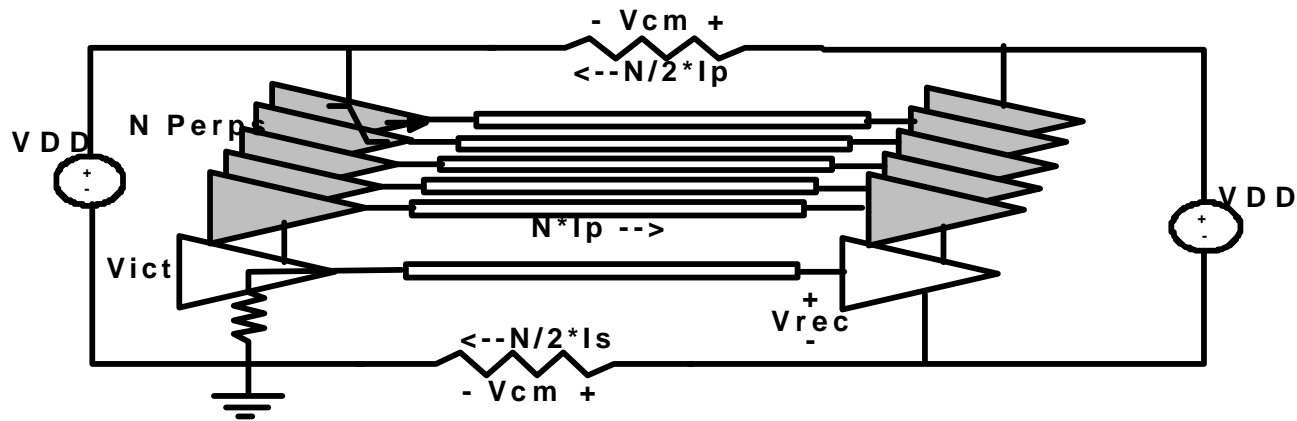
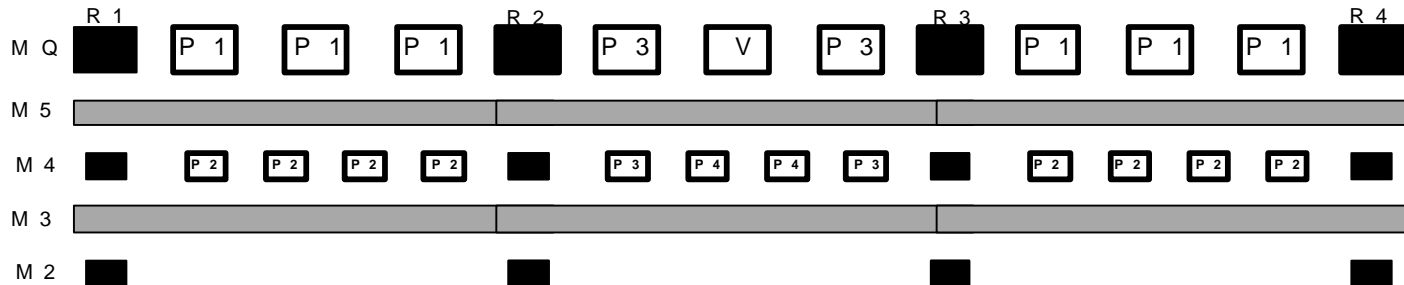
- Geometric
 - BEOL
 - power distribution
 - signal to power ratio
 - signal wiring patterns
- Coupling length
- Coupling location
- Net topology
 - signal direction
 - 1-drop, 2-drop, etc
 - capacitive loading
- Drive Strength
 - victim drv res
 - perp rise time
- 10-20x variation in noise level for a given coupled length





Common Mode Noise

- Drv to receiver voltage offset
 - ▶ Induced and displaced currents through resistive return path, $R_{ij}(f)$



Coupling and Common Mode Noise Evaluation Techniques

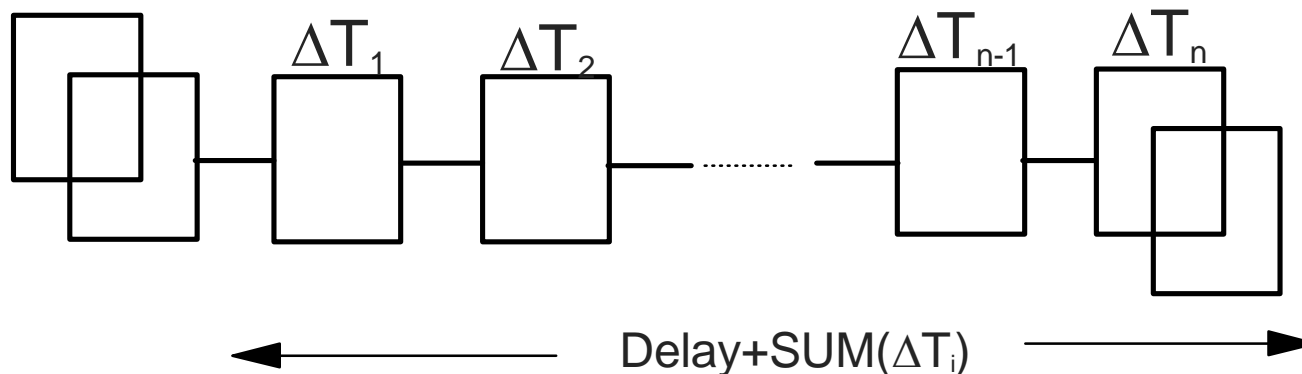
- Global level extraction (+200k nets)
 - RLC based
 - 3D capacitance
 - equations or table based
 - ◆ 10-15% error w.r.t. field solver solutions
 - ◆ Dynamic cap table build via field solvers(Rapheal, C2D)
 - 2D-R(f)L(f)
 - Extraction radius
 - ◆ narrow local coupling
 - ◆ wide for CMN? --> data volume issue
 - field solver or equations, i.e. Grover
 - ◆ PEEC, filament element
 - MOR or circuit synthesis for time domain simulations
 - Turn around time(TAT)
 - Production level performance
 - <8hrs
 - parallel processing techniques
 - Tools: 3DX(IBM internal), Columbus

Coupled and Common Mode Noise Evaluation Technique

- Coupling topology netlister
 - ▶ complete network representation of victim and aggressor nets
 - ▶ RLC circuit simulations using linear circuit solvers
 - parasitic data
 - pin capacitances
 - drv impedance/slews
 - linear model representation
 - ▶ peak noise @ receivers
 - superposition of noise sources based on timing overlap
 - ▶ functional fail criteria for a net
 - peak noise > noise limit within WOV
 - ▶ Tools: 3DNoise(RLC chip level, IBM internal), IBMmlsa(RC macro level, IBM internal), CADMOS

Coupled and Common Mode Noise Evaluation Technique

- Path based noise jitter effects accounted for in static timing
 - Static RC coupling approach
 - Uplift C_{total} by $K \cdot C_{ij}$
 - adjust windows
 - iterate
 - chicken and egg issue
 - RLC solutions ??
 - Tools: Einistimer(IBM internal)



Differential Power Supply Noise

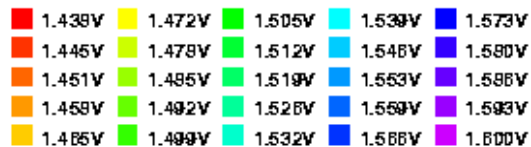
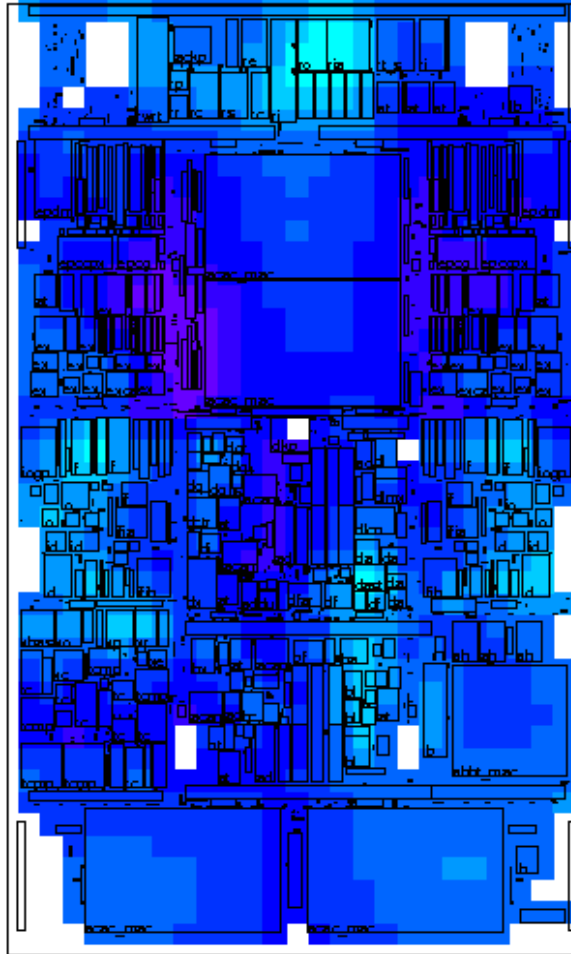
- Local and global power supply disturbance
 - IR drops
 - resistive power grid model
 - avg power assumption @ macro level
 - high frequency response
 - RL power grid model, on-chip capacitance
 - macro level transient load currents
 - load variations through resonant structures
- Resonance response
 - factored against DC operating condition
 - chip/package interface ~ 100 mhz
 - package inductance, on-chip capacitance
 - 1st/2nd level pkg design ~ 1-50mhz
 - Regulator Feedback --> 1khz - 1mhz
- High frequency response
 - circuit noise margin penalty
 - noise budget component

Differential PS Noise Evaluation Technique

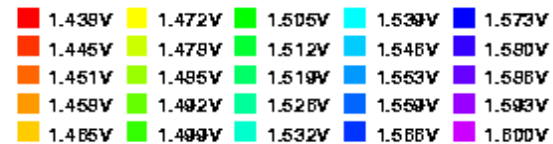
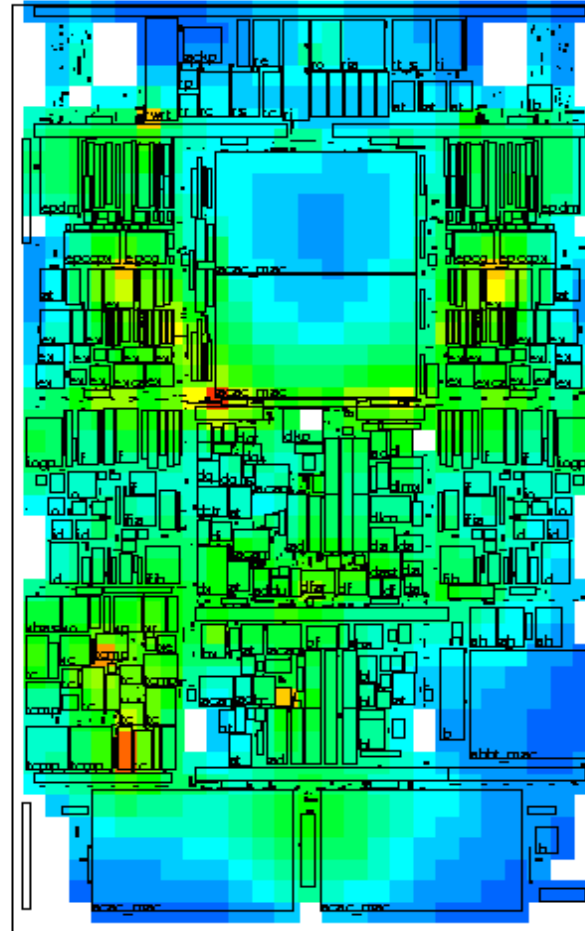
- Full chip evaluation process
 - ▶ RL segment models of chip power grid
 - coalesce power grid shapes to reduce model size
 - independent calculation of loop inductance via field solvers
 - ▶ VDD-GND current sources to represent circuit Loads
 - vector based power calculator for each macro/circuit
 - fast circuit simulations using piece wise linear device models
 - ▶ intrinsic capacitance(gate, nwell, wire) estimation from layouts
 - area/perimeter calculations
 - ▶ added decaps projected into model from chip floorplan
 - ▶ evaluation performed using fast linear simulator techniques
- Evaluation yields
 - ▶ VDD-GND collapse
 - chip/pkg resonance (when pkg model included)
 - high frequency noise
 - ▶ decap effectiveness
- Tools: NOVA, RAPID and ALSIM(IBM internal), Simplex, etc.

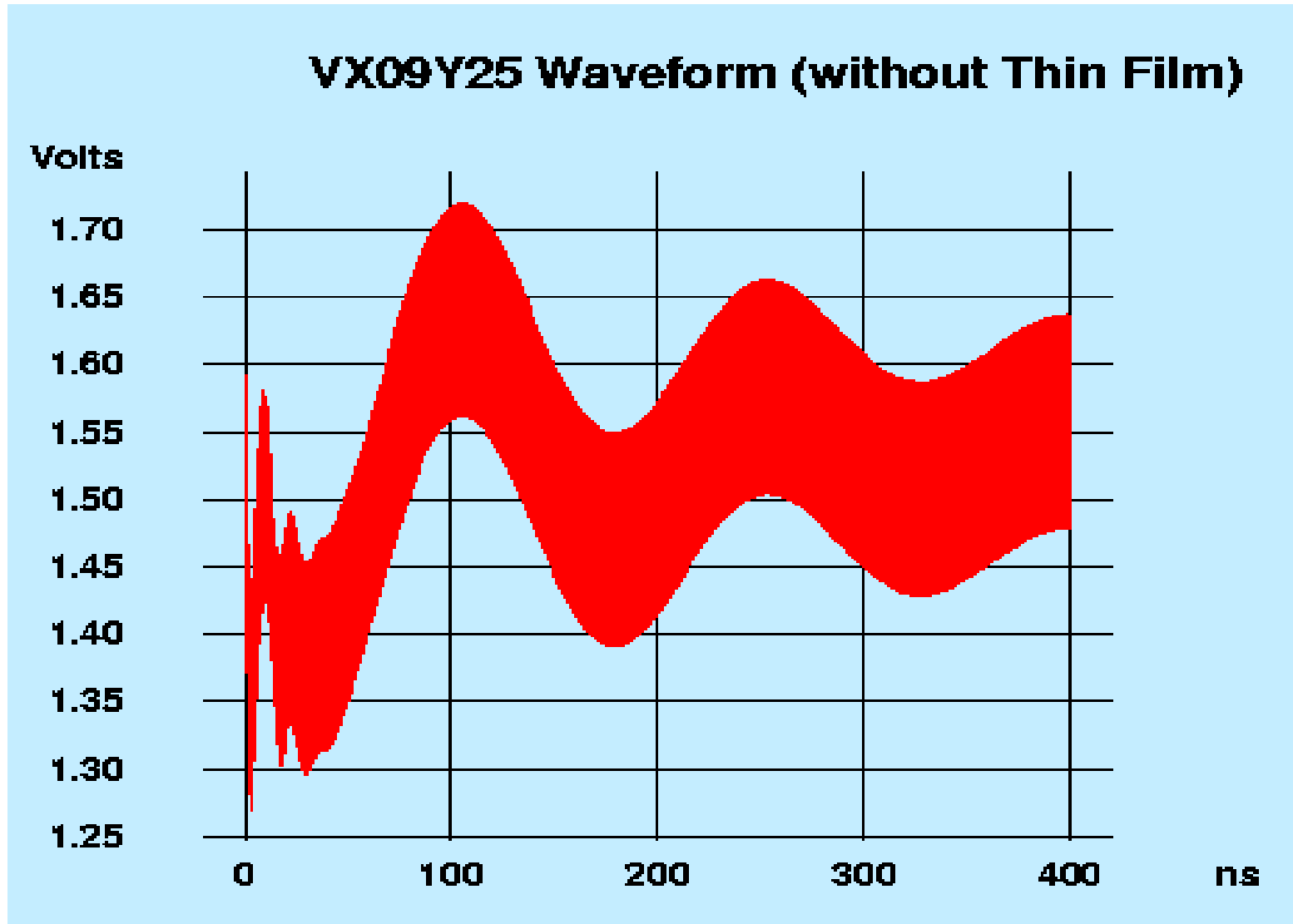
Differential PS Contour Map

On-Chip Vdd Distribution (T = T0 + 13.30 ns)



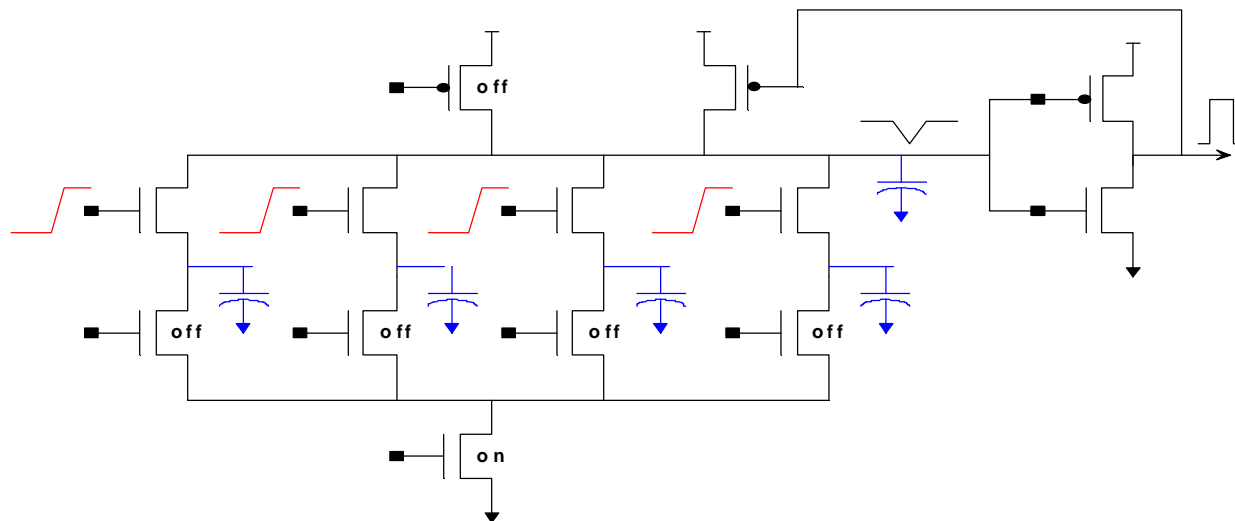
On-Chip Vdd Distribution (T = T0 + 13.70 ns)





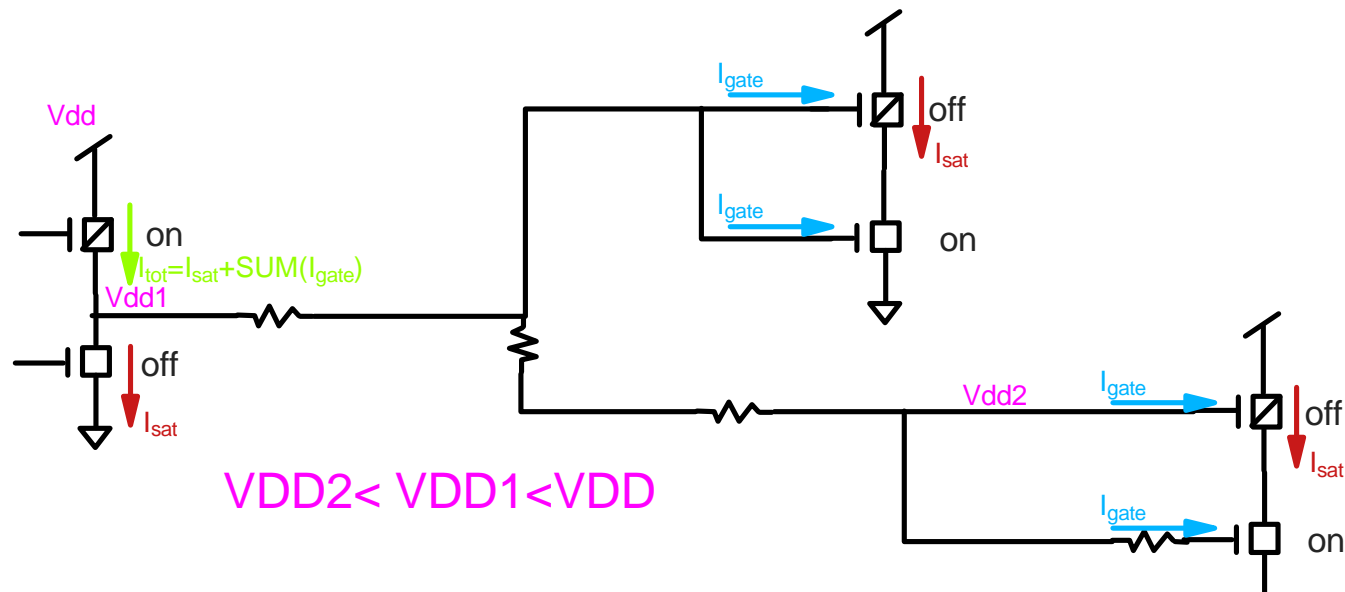
Charge Sharing

- Charge redistribution within internal circuit nodes
 - circuit design dependent
 - dynamic or weak static node
 - stacked devices
- Transistor level simulations
 - piece wise linear device models to decrease evaluation time
 - circuit topology recognition
 - input pattern dependency
 - Tools: IBMmlsa(IBM internal), CADMOS

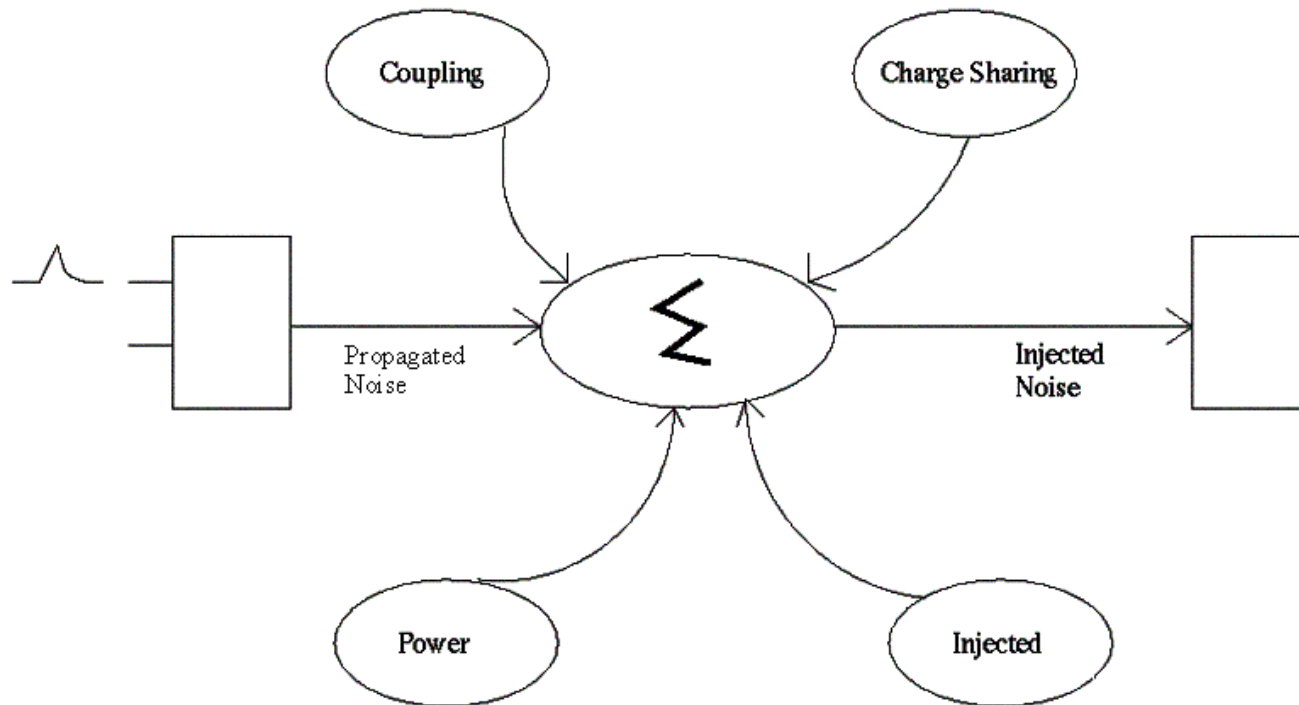


Circuit Leakage

- Device Leakage due to deep sub-micron scaling
 - Lower subthreshold voltage increasing I_{sat}
 - inverse temp dependency, manufacturing variations
 - Thinning gate oxide --> "tunneling effects" increasing I_{gate}
- Leakage biasing of circuit levels reduces circuit noise margins
- Transistor Level simulations
 - accurate device modeling in subthreshold region??
 - Resistance extraction of signal wires
- Tools: IBMmlsa(IBM internal), CADMOS?



Summation of Noise Sources in Digital Circuits (Noise Budget)



- Summation of quasi independent calculation processes

Future Tool Needs

- Full-chip $R(f)L(f)C$ extraction process for comprehensive evaluation of coupling/common mode noise
 - efficient wide radius techniques
 - TAT
 - netlisting into simulator
 - MOR
- Combined noise and timing calculators
 - in-core timing information
 - common netlisting procedure
 - timing, functional noise, noise effects on timing
 - transistor and rules based approaches
 - Complete Interlock to account for all noise sources
 - **fast non-linear simulation techniques**

Future Tool Needs

- Combined evaluation of CN/CMN/PS interactions
 - ▶ current loop assumptions inconsistent at circuit ports
 - zero VDD-GND impedance for CN/CMN
 - introduction of multiple power rails
 - ◆ discontinuous current return loops possible
 - VDD-GND current loop for PS
 - VDD or GND to Signal
 - ▶ Comprehensive $R(f)L(f)C$ extraction and device level simulation of combined interconnect/PS problem " The Holy Grail ! "
 - full chip evaluation ??
 - device and parasitic extraction process
 - very fast circuit simulation capabilities
 - circuit switching statistics an issue
 - ◆ dynamic simulations
 - ◆ pattern dependency and switching times uncertainties
 - ▶ LEXSIM from Nassada satisfies some of the above requirements
 - Macro based
 - RC netlist reduction
 - fast circuit simulation